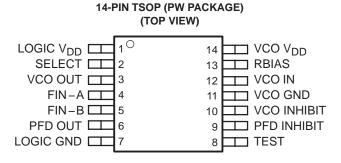
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- VCO (Voltage-Controlled Oscillator):
- Complete Oscillator Using Only One External Bias Resistor (RBIAS)
- Lock Frequency: 30 MHz to 55 MHz (VDD = 3 V  $\pm$ 5%, T<sub>A</sub> = -20°C to 75°C, x1 Output) 30 MHz to 60 MHz (VDD = 3.3 V  $\pm$ 5%, T<sub>A</sub> = -20°C to 75°C, x1 Output) 43 MHz to 110 MHz (VDD = 5 V  $\pm$ 5%, T<sub>A</sub> = -20°C to 75°C, x1 Output)
- Selectable Output Frequency
- PFD (Phase Frequency Detector): High Speed, Edge-Triggered Detector with Internal Charge Pump

- Independent VCO, PFD Power-Down Mode
- Thin Small-Outline Package (14 Terminal)
- CMOS Technology
- Pin Compatible TLC2933IPW



### description

The TLC2933A is designed for phase-locked loop (PLL) systems and is composed of a voltage-controlled oscillator (VCO) and an edge-triggered type phase frequency detector (PFD). The oscillation frequency range of the VCO is set by an external bias resistor ( $R_{BIAS}$ ). The VCO has a 1/2 frequency divider at the output stage. The high speed PFD with internal charge pump detects the phase difference between the reference frequency input and signal frequency input from the external counter. Both the VCO and the PFD have inhibit functions, which can be used as power-down mode. Due to the TLC2933A high speed and stable oscillation capability, the TLC2933A is suitable for use as a high-performance PLL.

#### AVAILABLE OPTIONS

-	PACKAGE
٩	SMALL OUTLINE (PW)
–20°C to 75°C	TLC2933AIPW



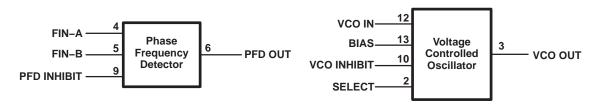
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### functional block diagram



### **Terminal Functions**

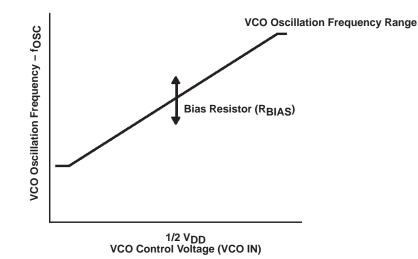
TERMINA	L		DECODIDATION
NAME	NO.	I/O	DESCRIPTION
LOGIC VDD	1		Power supply for the internal logic. This power supply should be separated from VCO $V_{\mbox{DD}}$ to reduce cross-coupling between supplies.
SELECT	2	I	VCO output frequency select. When SELECT is high, the VCO output frequency is $\times 1/2$ and when low. The output frequency is $\times 1$ .
VCO OUT	3	0	VCO output. When the VCO INHIBIT is high, VCO output is low.
FIN–A	4	I	Input reference frequency f <sub>(REF IN)</sub> is applied to FIN–A.
FIN-B	5	I	Input for VCO external counter output frequency f <sub>(FIN-B)</sub> . FIN-B is nominally provided from the external counter.
PFD OUT	6	0	PFD output. When the PFD INHIBIT is high, PFD output is in the high-impedance state.
LOGIC GND	7		GND for the internal logic.
TEST	8		Connect to GND.
PFD INHIBIT	9	I	PFD inhibit control. When PFD INHIBIT is high, PFD output is in the high-impedance state.
VCO INHIBIT	10	I	VCO inhibit control. When VCO INHIBIT is high, VCO output is low.
VCO GND	11		GND for VCO.
VCO IN	12	I	VCO control voltage input. Nominally the external loop filter output connects to VCO IN to control VCO oscillation frequency.
RBIAS	13	I	Bias supply. An external resistor (R <sub>BIAS</sub> ) between VCO V <sub>DD</sub> and R <sub>BIAS</sub> supplies bias for adjusting the oscillation frequency range.
VCO V <sub>DD</sub>	14		Power supply for VCO. This power supply should be separated from LOGIC V <sub>DD</sub> to reduce cross-coupling between supplies.



### detailed description

#### VCO oscillation frequency

The VCO oscillation frequency is determined by an external register ( $R_{BIAS}$ ) connected between the VCO  $V_{DD}$  and the BIAS terminals. The oscillation frequency and range depends on this Resistor value. For the lock frequency range, refer to the recommended operating conditions. Figure 1 shows the typical frequency variation and VCO control voltage.



### **Figure 1. Oscillation Frequency**

#### VCO output frequency 1/2 divider

The TLC2933A SELECT terminal sets the  $f_{OSC}$  VCO output frequency as shown in Table 1. The 1/2  $f_{OSC}$  output should be used for minimum VCO output jitter.

SELLECT	VCO OUTPUT
Low	fosc
High	1/2 fosc

### Table 1. VCO Output 1/2 Divider Function

#### **VCO** inhibit function

The VCO has an externally controlled inhibit function which inhibit the VCO output. A high level on the VCO INHIBIT terminal stops the VCO oscillation and powers down the VCO. The output maintains a low level during the power–down mode as shown in Table 2.

**Table 2. VCO Inhibit Function** 

	VCO INHIBIT	VCO OSCILLATOR	VCO OUT	IDD(VCO)
Γ	Low	Active	Active	Normal
	High	Stopped	Low level	Power Down

#### **PFD** operation

The PFD is a high-speed, edge-triggered detector with an internal charge pump. The PFD detects the phase difference between two frequency inputs supplied to FIN–A and FIN–B as shown in Figure 2. Normally the reference is supplied to FIN–A and the frequency from the external counter output is fed to FIN–B. For clock recovery PLL system, other types of phase detectors should be used.



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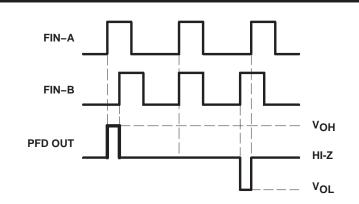


Figure 2. PFD Function Timing Chart

#### **PFD** inhibit control

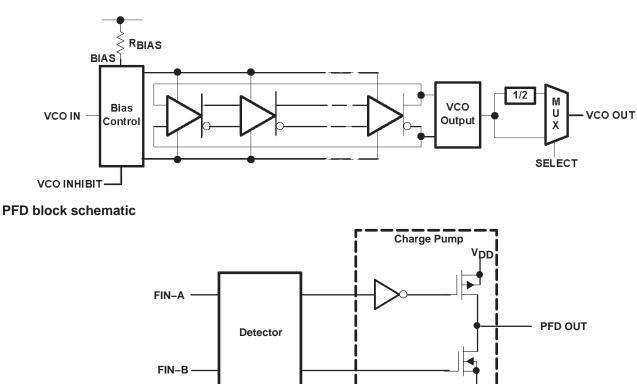
A high level on the PFD INHIBIT terminal places PFD OUT in the high-impedance state and the PFD stops phase detection as shown in Table 3. A high level on the PFD INHIBIT terminal can also be used as the power-down mode for the PFD.

 Table 3. VCO Output Control Function

PFI	D INHIBIT	DETECTION	PFD OUT	IDD(PFD)
	Low	Active	Active	Normal
	High	Stopped	Hi–Z	Power Down

### VCO block schematic

PFD INHIBIT -





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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage (each supply), V <sub>DD</sub> (see Note 1)	
Input voltage range (each input), V <sub>IN</sub> (see Note 1)	–0.5 V to V <sub>DD</sub> + 0.5 V
Input current (each input), I <sub>IN</sub>	±20 mA
Output current (each output), I <sub>O</sub>	±20 mA
Operating free-air temperature range, T <sub>A</sub>	–20°C to 75°C
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to GND.

2. For operation above 25°C free-air temperature, derate linearly at the rate of 5.6 mW/°C.

PARA	METERS	MIN	ТҮР	MAX	UNIT	
	$V_{DD} = 3 V$	2.85	3	3.15		
Supply voltage (each supply, see Note 3)	V <sub>DD</sub> = 3.3 V	3.135	3.3	3.465	V	
	V <sub>DD</sub> = 5 V	4.75	5	5.25		
Input voltage, (inputs except VCO IN)		0		Vdd	V	
Output current, (each output)		0		±2	mA	
VCO control voltage at VCO IN		0.9		VDD	V	
	$V_{DD} = 3 V$	30		55		
Lock frequency	V <sub>DD</sub> = 3.3 V	30		60	MHz	
	$V_{DD} = 5 V$	43		110		
Bias resisitor	$V_{DD} = 3 V$	2.2		5.1		
	V <sub>DD</sub> = 3.3 V	2.2		5.1	kΩ	
	$V_{DD} = 5 V$	2.2		5.1		

#### recommended operating conditions

NOTE 3: It is recommended that the logic supply terminal (LOGIC V<sub>DD</sub>) and the VCO supply terminal (VCO V<sub>DD</sub>) should be at the same voltage and separated from each other.

### electrical characteristics, $V_{DD}$ = 3 V, $T_A$ = 25°C (unless otherwise noted)

#### VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	$I_{OH} = -2 \text{ mA}$	2.4			V
VOL	Low level output voltage	$I_{OL} = 2 \text{ mA}$			0.3	V
V <sub>TH</sub>	Input threshold voltage at select, VCO inhibit		0.9	1.5	2.1	V
Ц	Input current at Select, VCO inhibit	V <sub>I</sub> = V <sub>DD</sub> or GND			±1	μΑ
ZI(VCON)	VCO IN input impedance	VCO IN = $1/2 V_{DD}$		10		MΩ
IDD(INH)	VCO supply current (inhibit)	See Note 4		0.41	1	μΑ
IDD(VCO)	VCO supply current	See Note 5		11.7	23	mA

NOTES: 4. Current into VCO V<sub>DD</sub>, when VCO INHIBIT = high, PFD is inhibited.

5. Current into VCO V<sub>DD</sub>, when VCO IN = 1/2 V<sub>DD</sub>, R<sub>BIAS</sub> = 3.3 kΩ, VCOOUT = 15-pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.



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### electrical characteristics, $V_{DD}$ = 3 V, $T_A$ = 25°C (unless otherwise noted) (continued)

### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	I <sub>OH</sub> = -2 mA	2.4			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.3	V
I <sub>OZ</sub>	High impedance state output current	PFD inhibit = high, $V_O = V_{DD}$ or GND			±1	μA
VIH	High level input voltage at Fin–A, Fin–B		2.1			V
VIL	Low level input voltage at Fin–A, Fin–B				0.5	V
V <sub>TH</sub>	Input threshold voltage at PFD inhibit		0.9	1.5	2.1	
C <sub>IN</sub>	Input capacitance at Fin-A, Fin-B			5.6		pF
Z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		MΩ
IDD(Z)	High impedance state PFD supply current	See Note 6			1	μA
IDD(PFD)	PFD supply current	See Note 7			3	mA

NOTES: 6. The current into LOGIC V<sub>DD</sub> when FIN–A and FIN–B = ground, PFD INHIBIT = V<sub>DD</sub>, PFD OUT open, and VCO OUT is inhibited. 7. The current into LOGIC V<sub>DD</sub> when FIN–A = 1 MHz and FIN–B = 1 MHz ( $V_{I(PP)}$  = 3 V, rectangular wave), PFD INHIBIT = GND, PFD OUT open, and VCO OUT is inhibited.

### operation characteristics, $V_{DD}$ = 3 V, $T_A$ = 25°C (unless otherwise noted)

#### **VCO** section

	Parameter	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fosc	Operation oscillation frequency	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	32	47	63	MHz
fSTB	Time to stable oscillation (see Note 8)				10	μs
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		8.6	14	ns
t <sub>f</sub>	Fall time	C <sub>L</sub> = 15 pF		7.1	12	ns
	Duty cycle at VCO OUT	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	45%	50%	55%	
$\alpha$ (fOSC)	Temperature coefficient of oscillation frequency	VCO IN = $1/2 V_{DD}$ , T <sub>A</sub> = $-20^{\circ}$ C to $75^{\circ}$ C		-0.21		%/°C
k <sub>SVS</sub> (fosc)	Supply voltage coefficient of oscillation frequency	VCO IN = $1/2 V_{DD}$ , V <sub>DD</sub> = $4.75 V \text{ to } 5.25 V$		0.002		%/mV
	Jitter absolute (see Note 9)	PLL jitter, N = 128		262		ps

NOTES: 8. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.

9. Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.

#### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fmax	Maximum operation frequency		32			MH
<sup>t</sup> PLZ	PFD output disable time from low level			22	50	ns
<sup>t</sup> PHZ	PFD output disable time from high level			21	50	ns
<sup>t</sup> PZL	PFD output enable time to low level			6.5	30	ns
<sup>t</sup> PZH	PFD output enable time to high level			7	30	ns
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		3.4	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		1.9	10	ns



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## electrical characteristics, $V_{DD}$ = 3.3 V, $T_A$ = 25°C (unless otherwise noted)

#### VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	$I_{OH} = -2 \text{ mA}$	2.64			V
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = 2 mA			0.33	V
$V_{TH}$	Input threshold voltage at select, VCO inhibit		1.05	1.65	2.25	V
lj	Input current at Select, VCO inhibit	$V_I = V_{DD}$ or GND			±1	μΑ
ZI(VCON)	VCO IN input impedance	VCO IN = $1/2 V_{DD}$		10		MΩ
IDD(INH)	VCO supply current (inhibit)	See Note 10		0.44	1	μΑ
IDD(VCO)	VCO supply current	See Note 11		14.7	28	mA

NOTES: 10. Current into VCO V<sub>DD</sub>, when VCO INHIBIT = high, PFD is inhibited.

11. Current into VCO V<sub>DD</sub>, when VCO IN =  $1/2 V_{DD}$ , R<sub>BIAS</sub> = 3.3 k $\Omega$ , VCOOUT = 15-pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.

#### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	I <sub>OH</sub> = -2 mA	2.97			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.2	V
IOZ	High impedance state output current	PFD inhibit = high, $V_O = V_{DD}$ or GND			±1	μΑ
VIH	High level input voltage at Fin–A, Fin–B		2.1			V
VIL	Low level input voltage at Fin–A, Fin–B				0.5	V
VTH	Input threshold voltage at PFD inhibit		1.05	1.65	2.25	
CIN	Input capacitance at Fin-A, Fin-B			5.6		pF
z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		MΩ
IDD(Z)	High impedance state PFD supply current	See Note 12			1	μΑ
IDD(PFD)	PFD supply current	See Note 13			3	mA

NOTES: 12. The current into LOGIC V<sub>DD</sub> when FIN–A and FIN–B = ground, PFD INHIBIT = V<sub>DD</sub>, PFD OUT open, and VCO OUT is inhibited. 13. The current into LOGIC V<sub>DD</sub> when FIN–A = 1 MHz and FIN–B = 1 MHz ( $V_{I(PP)}$  = 3.3 V, rectangular wave), PFD INHIBIT = GND, PFD OUT open, and VCO OUT is inhibited.

### operation characteristics, $V_{DD}$ = 3.3 V, $T_A$ = 25°C (unless otherwise noted)

### VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fosc	Operation oscillation frequency	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 VDD	35	55	80	MHz
fstb	Time to stable oscillation (see Note 14)				10	μs
tr	Rise time	C <sub>L</sub> = 15 pF		8.3	14	ns
tf	Fall time	C <sub>L</sub> = 15 pF		6.7	12	ns
fduty	Duty cycle at VCO OUT	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 VDD	45%	50%	55%	
$\alpha$ (f <sub>OSC</sub> )	Temperature coefficient of oscillation frequency	VCO IN = 1/2 VDD, $T_A = -20^{\circ}C$ to 75°C		-0.232		%/°C
ksvs(fosc)	Supply voltage coefficient of oscillation frequency	VCO IN = 1/2 $V_{DD}$ , $V_{DD}$ = 4.75 V to 5.25 V		0.002		%/m V
	Jitter absolute (see Note 15)	PLL jitter, N = 128		211		ps

NOTES: 14. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.

15. Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.



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# operation characteristics, $V_{DD}$ = 3.3 V, $T_A$ = 25°C (unless otherwise noted) (continued)

#### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
fmax	Maximum operation frequency		40			MHz
<sup>t</sup> PLZ	PFD output disable time from low level			21	50	ns
<sup>t</sup> PHZ	PFD output disable time from high level			21	50	ns
<sup>t</sup> PZL	PFD output enable time to low level			5.8	30	ns
<sup>t</sup> PZH	PFD output enable time to high level			6.2	30	ns
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		3	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		1.7	10	ns

### electrical characteristics, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

#### VCO section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	$I_{OH} = -2 \text{ mA}$	4			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.5	V
V <sub>TH</sub>	Input threshold voltage at select, VCO inhibit		1.5	2.5	3.5	V
lj	Input current at select, VCO inhibit	$V_{I} = V_{DD}$ or GND			±1	μΑ
ZI(VCON)	VCO IN input impedance	VCO IN = $1/2$ V <sub>DD</sub>		10		M(
IDD(inh)	VCO supply current (inhibit)	See Note 16		0.61	1	μΑ
IDD(vco)	VCO supply current	See Note 17		35.5	55	mA

NOTES: 16. Current into VCO  $V_{DD}$ , when VCO INHIBIT = high, PFD is inhibited.

17. Current into VCO V<sub>DD</sub>, when VCO IN = 1/2 V<sub>DD</sub>, R<sub>BIAS</sub> = 3.3 k $\Omega$ , VCOOUT = 15-pF Load, VCO INHIBIT = GND, and PFD INHIBIT = GND.

#### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High level output voltage	I <sub>OH</sub> = -2 mA	4.5			V
VOL	Low level output voltage	I <sub>OL</sub> = 2 mA			0.2	V
I <sub>OZ</sub>	High impedance state output current	PFD inhibit = high, $V_0 = V_{DD}$ or GND			±1	μΑ
VIH	High level input voltage at Fin–A, Fin–B		4.5			V
VIL	Low level input voltage at Fin–A, Fin–B				1	V
VTH	Input threshold voltage at PFD inhibit		1.5	2.5	3.5	
CIN	Input capacitance at Fin-A, Fin-B			5.6		pF
Z <sub>IN</sub>	Input impedance at Fin-A, Fin-B			10		MΩ
IDD(Z)	High impedance state PFD supply current	See Note 18			1	μA
IDD(PFD)	PFD supply current	See Note 19		0.48	3	mA

NOTES: 18. The current into LOGIC V<sub>DD</sub> when FIN–A and FIN–B = ground, PFD INHIBIT = V<sub>DD</sub>, PFD OUT open, and VCO OUT is inhibited.
 19. The current into LOGIC V<sub>DD</sub> when FIN–A = 1 MHz and FIN–B = 1 MHz (V<sub>I(PP)</sub> = 5 V, rectangular wave), PFD INHIBIT = GND, PFD OUT open, and VCO OUT is inhibited



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# operation characteristics, $V_{DD} = 5 V$ , $T_A = 25^{\circ}C$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
fosc	Operation oscillation frequency	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	70	99	130	MHz	
<sup>f</sup> STB	Time to stable oscillation (see Note 20)				10	us	
t <sub>r</sub>	Rise time	C <sub>L</sub> = 15 pF		5.4	10	ns	
t <sub>f</sub>	Fall time	C <sub>L</sub> = 15 pF		5	10	ns	
fduty	Duty cycle at VCO OUT	$R_{BIAS} = 3.3 \text{ k}\Omega$ , VCO IN = 1/2 $V_{DD}$	45%	50%	55%		
$\alpha$ (fOSC)	Temperature coefficient of oscillation frequency	VCO IN = 1/2 V <sub>DD</sub> , $T_A = -20^{\circ}C$ to 75°C		-0.309		%/°C	
ksvs(fos C)	Supply voltage coefficient of oscillation frequency	VCO IN = 1/2 V <sub>DD</sub> , V <sub>DD</sub> = 4.75 V to 5.25 V		0.001		%/mV	
	Jitter absolute (see Note 21)	PLL jitter, N = 128		140		ps	

NOTES: 20. The time period to the stable VCO oscillation frequency after the VCO INHIBIT terminal is changed to a low level.

21. Jitter performance is highly dependent on circuit layout and external device characteristics. The jitter specification was made with a carefully deigned PCB with no device socket.

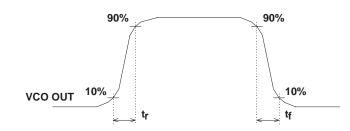
#### **PFD** section

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f <sub>max</sub>	Maximum operation frequency		65			MHz
<sup>t</sup> PLZ	PFD output disable time from low level			20	40	ns
<sup>t</sup> PHZ	PFD output disable time from high level			20	40	ns
<sup>t</sup> PZL	PFD output enable time to low level			4	20	ns
<sup>t</sup> PZH	PFD output enable time to high level			4.3	20	ns
tr	Rise time	C <sub>L</sub> = 15 pF		2.1	10	ns
tf	Fall time	C <sub>L</sub> = 15 pF		1.3	10	ns



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### PARAMETER MEASUREMENT INFORMATION



### Figure 3. VCO Output Voltage Waveform

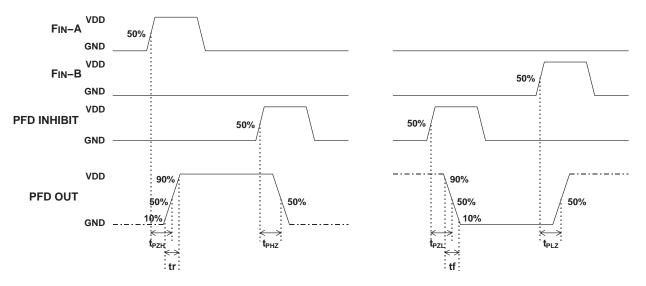


Figure 4. PFD Output Voltage Waveform

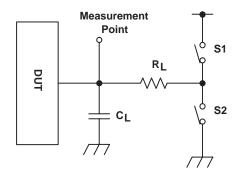
# Table 4. PFD Output Test Conditions

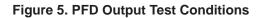
PARAMETER	RL	CL	S1	S2			
<sup>t</sup> PZH	-						
<sup>t</sup> PHZ			OPEN	CLOSE			
tr	1 kΩ	15 pF					
<sup>t</sup> PZL							
<sup>t</sup> PLZ			CLOSE	OPEN			
tf							



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### PARAMETER MEASUREMENT INFORMATION





### **TYPICAL CHARACTERISTICS**

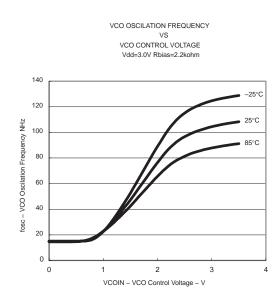


Figure 6.



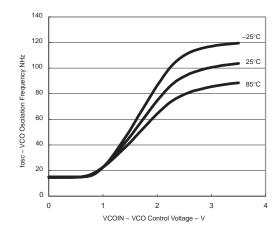
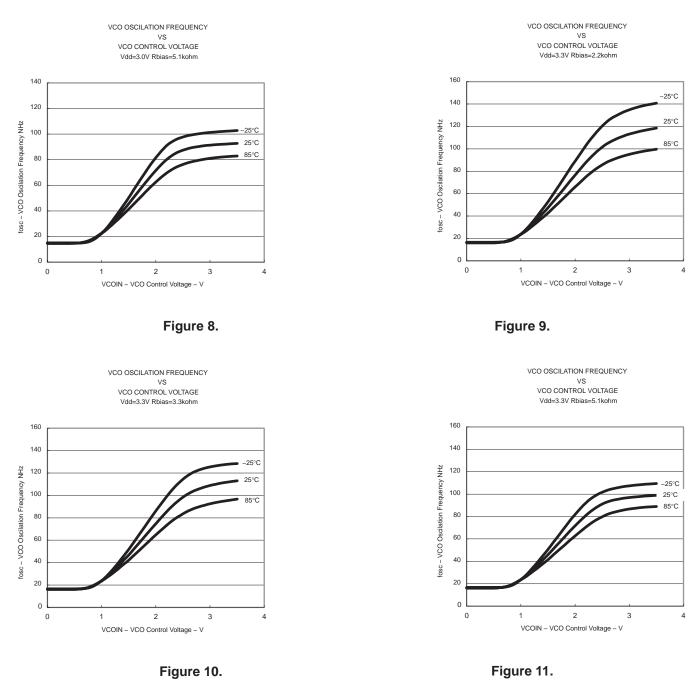


Figure 7.



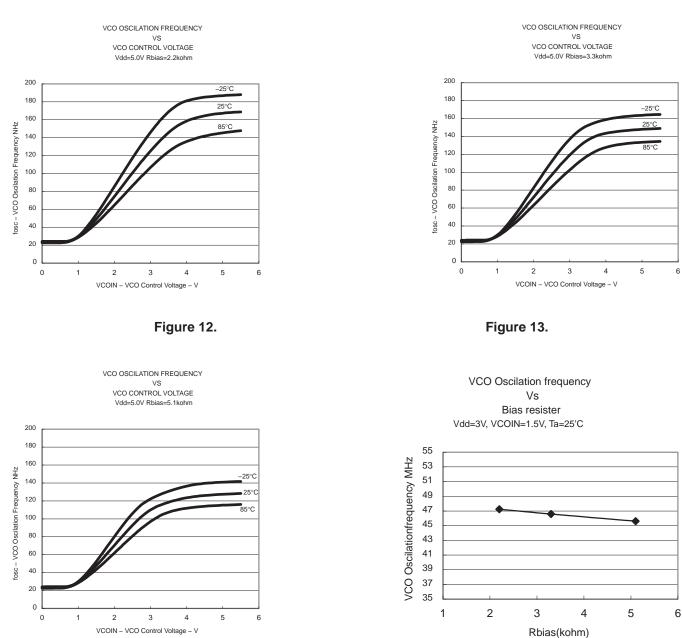
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### **TYPICAL CHARACTERISTICS**





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### **TYPICAL CHARACTERISTICS**

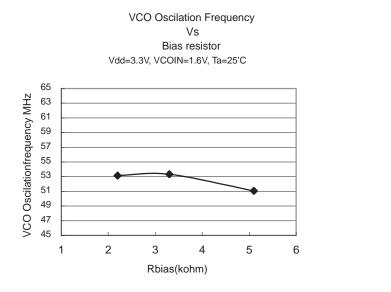
Figure 14.

Figure 15.

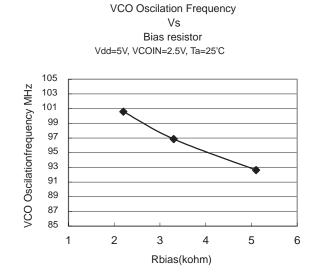


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### TYPICAL CHARACTERISTICS









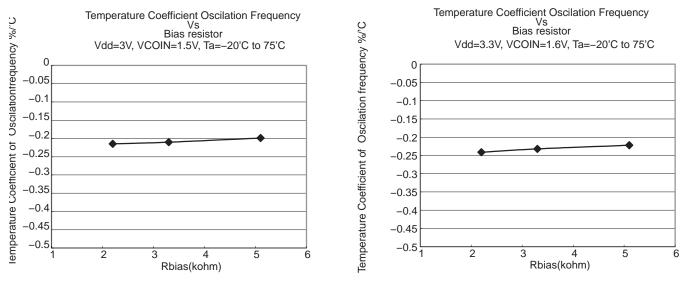




Figure 19.



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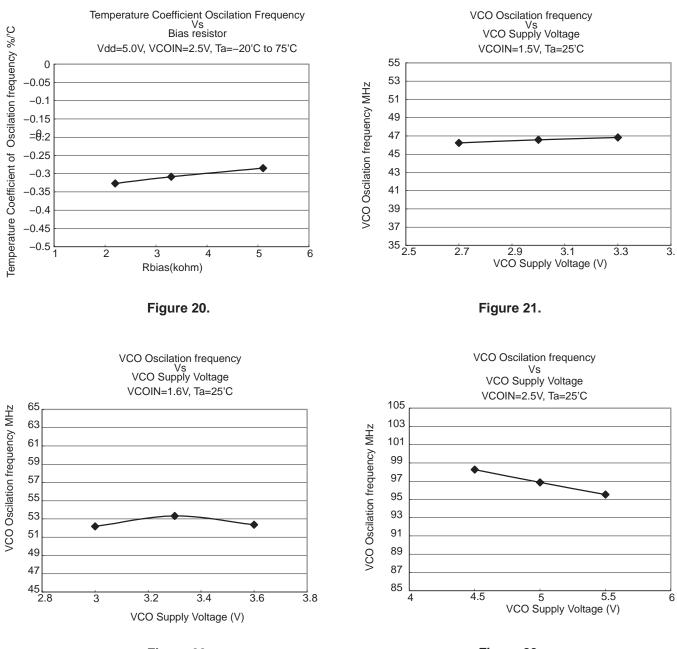


Figure 22.

Figure 23.



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## TYPICAL CHARACTERISTICS

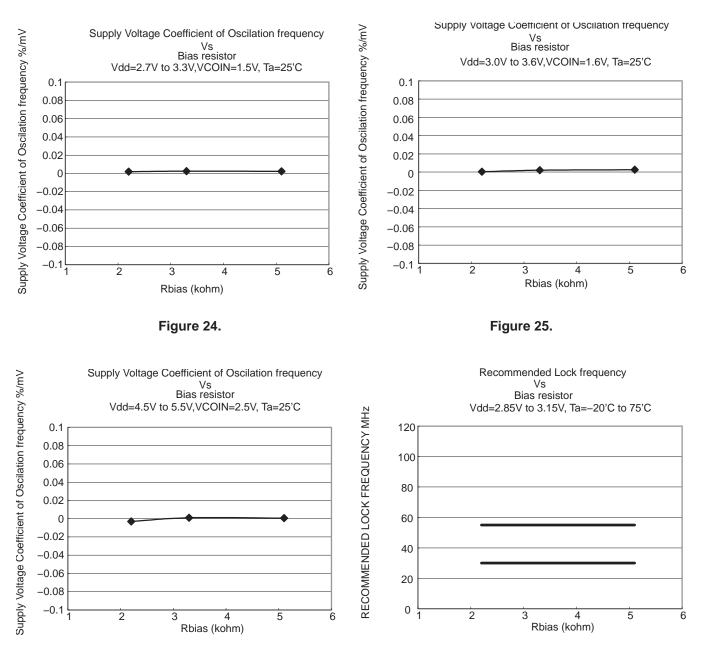
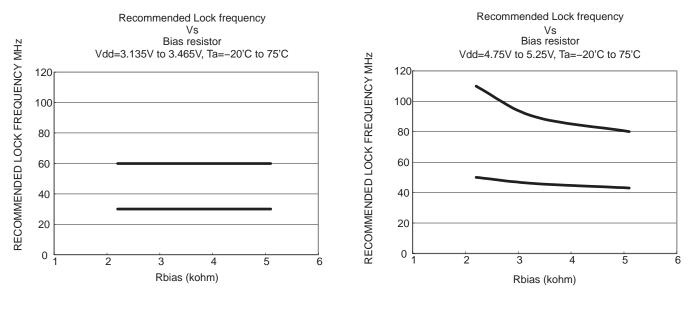


Figure 26.

Figure 27.



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### **TYPICAL CHARACTERISTICS**

Figure 28.

Figure 29.





### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing		Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TLC2933AIPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2933A	Samples
TLC2933AIPWG4	LIFEBUY	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2933A	
TLC2933AIPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-20 to 75	Y2933A	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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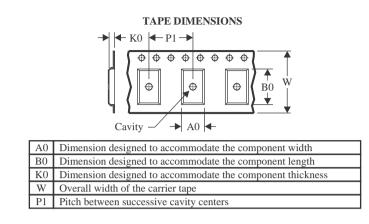


Texas

STRUMENTS

### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	
-----------------------------	--

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC2933AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

3-Jun-2022



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC2933AIPWR	TSSOP	PW	14	2000	356.0	356.0	35.0

### TEXAS INSTRUMENTS

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### TUBE



## - B - Alignment groove width

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TLC2933AIPW	PW	TSSOP	14	90	530	10.2	3600	3.5
TLC2933AIPWG4	PW	TSSOP	14	90	530	10.2	3600	3.5

# **PW0014A**



# **PACKAGE OUTLINE**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0014A

# **EXAMPLE BOARD LAYOUT**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0014A

# **EXAMPLE STENCIL DESIGN**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



<sup>8.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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